



STD9NM60N STF9NM60N, STP9NM60N

N-channel 600 V, 0.63 Ω , 6.5 A TO-220, TO-220FP, DPAK
MDmesh™ II Power MOSFET

Features

| Order codes | V _{DSS} (@T _{jmax}) | R _{DS(on)} max. | I _D |
|-------------|---|-----------------------------|----------------|
| STD9NM60N | 650 V | < 0.745 Ω | 6.5 A |
| STF9NM60N | | | |
| STP9NM60N | | | |

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Application

Switching applications

Description

This series of devices is realized with the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

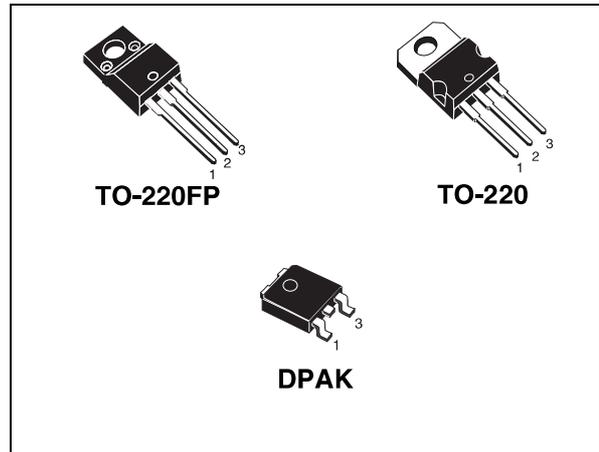


Figure 1. Internal schematic diagram

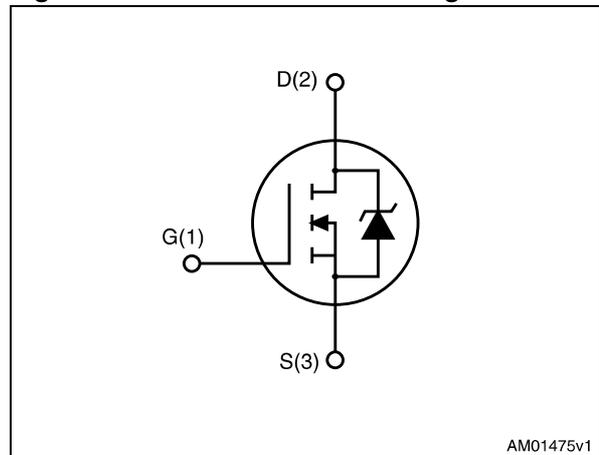


Table 1. Device summary

| Order codes | Marking | Packages | Packaging |
|-------------|---------|----------|---------------|
| STD9NM60N | 9NM60N | DPAK | Tape and reel |
| STF9NM60N | | TO-220FP | Tube |
| STP9NM60N | | TO-220 | |